

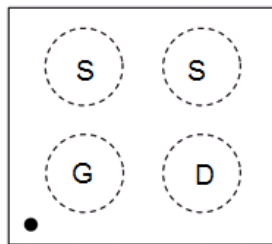
Product Summary (Typ @V_{GS} = -4.5V, T_A = +25°C)

BV _{DSS}	R _{DS(ON)}	Q _g	Q _{gd}	I _D
-12V	65mΩ	9nC	2.4nC	-3.2A

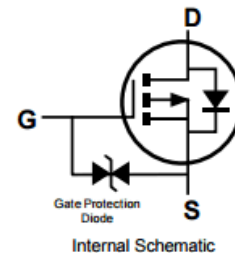
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications. It is a high-performance MOSFET in ultra-small 0.8mm x 0.8mm package.

- Portable Applications
- Load Switch
- Power Management Functions



Top View



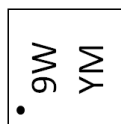
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1100UCB4-7	X2-WLB0808-4	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



9W = Product Type Marking Code
 YM = Date Code Marking
 Y or $\bar{Y}$ = Year (ex: D = 2016)
 M or $\bar{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022
Code	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-12	V
Gate-Source Voltage	V_{GSS}	± 8	V
Continuous Source Current @ $V_{GS} = -4.5V$ (Note 5)	I_D	-2.5 -2.0	A
Continuous Source Current @ $V_{GS} = -4.5V$ (Note 6)	I_D	-3.2 -2.6	A
Pulsed Drain Current (Pulse Duration 10 μ s, Duty Cycle $\leq 1\%$)	I_{DM}	-13	A
Continuous Source-Drain Diode Current	I_S	-1.2	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.67	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	187	$^{\circ}C/W$
Total Power Dissipation (Note 6)	P_D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	117	$^{\circ}C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}C$

Electrical Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS} = -12V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.35	-0.55	-0.8	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	65 80 90 115 135 150	83 96 150 170 300 400	m Ω	$V_{GS} = -4.5V, I_D = -3A$ $V_{GS} = -2.5V, I_D = -2A$ $V_{GS} = -1.8V, I_D = -1A$ $V_{GS} = -1.5V, I_D = -1A$ $V_{GS} = -1.4V, I_D = -1A$ $V_{GS} = -1.3V, I_D = -1A$
Forward Transfer Admittance	$ Y_{fs} $	-	6.5	-	S	$V_{DS} = -4V, I_S = -1.5A$
Body Diode Forward Voltage	V_{SD}	-	-0.7	-	V	$V_{GS} = 0V, I_S = -1.5A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	680	820	pF	$V_{DS} = -6V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	220	290	pF	
Reverse Transfer Capacitance	C_{rss}	-	205	280	pF	
Gate Resistance	R_g	-	11.2	17	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	-	9.0	14	nC	$V_{GS} = -4.5V, V_{DS} = -6V,$ $I_D = -2A$
Gate-Source Charge	Q_{gs}	-	1.0	-	nC	
Gate-Drain Charge	Q_{gd}	-	2.6	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	4.4	9	ns	$V_{DD} = -4V, I_D = -2A$ $V_{GEN} = -4.5V, R_g = 1\Omega, R_L = 3\Omega$
Turn-On Rise Time	t_R	-	10.1	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	22	33	ns	
Turn-Off Fall Time	t_F	-	20	-	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.

Electrical Characteristics (@T_A = 0°C.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
ON CHARACTERISTICS (Note 7,Note 8)						
Static Drain-Source On-Resistance	R _{DS(ON)}	-	62	83	mΩ	V _{GS} = -4.5V, I _D = -3A
			78	96		V _{GS} = -2.5V, I _D = -2A
			88	150		V _{GS} = -1.8V, I _D = -1A
			112	170		V _{GS} = -1.5V, I _D = -1A
			130	300		V _{GS} = -1.4V, I _D = -1A
			150	400		V _{GS} = -1.3V, I _D = -1A

Electrical Characteristics (@T_A = + 65°C.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
ON CHARACTERISTICS (Note 7,Note 8)						
Static Drain-Source On-Resistance	R _{DS(ON)}	-	73	93	mΩ	V _{GS} = -4.5V, I _D = -3A
			89	118		V _{GS} = -2.5V, I _D = -2A
			107	185		V _{GS} = -1.8V, I _D = -1A
			127	195		V _{GS} = -1.5V, I _D = -1A
			141	300		V _{GS} = -1.4V, I _D = -1A
			163	400		V _{GS} = -1.3V, I _D = -1A

Note: 8. Guaranteed by design. Not subject to production testing.

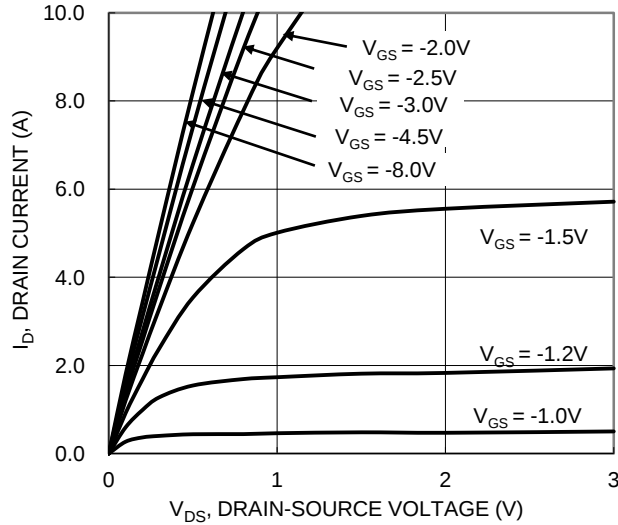


Figure 1. Typical Output Characteristic

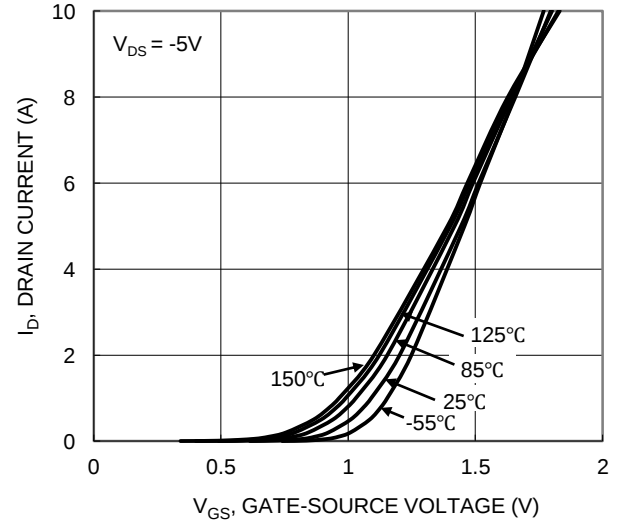


Figure 2. Typical Transfer Characteristic

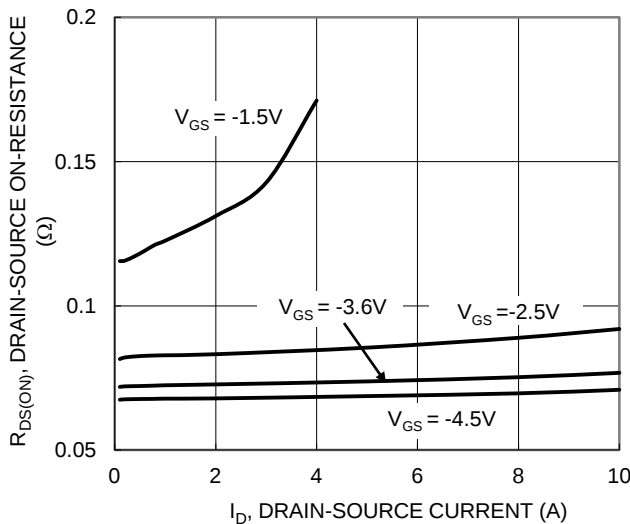


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

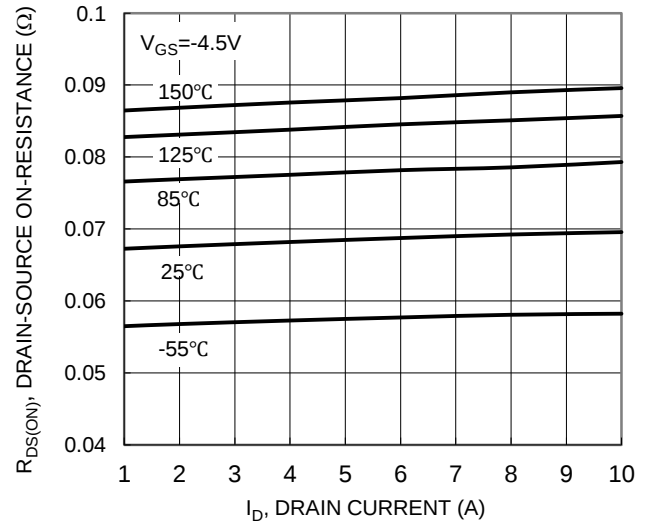


Figure 4. Typical On-Resistance vs. Drain Current and Junction Temperature

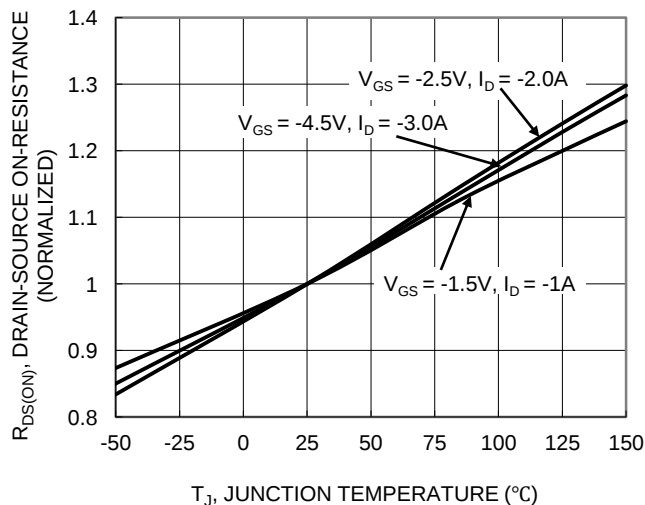


Figure 5. On-Resistance Variation with Junction Temperature

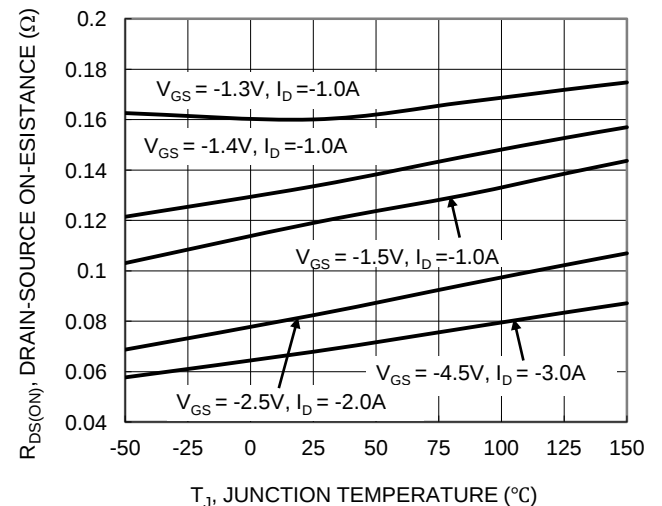


Figure 6. On-Resistance Variation with Junction Temperature

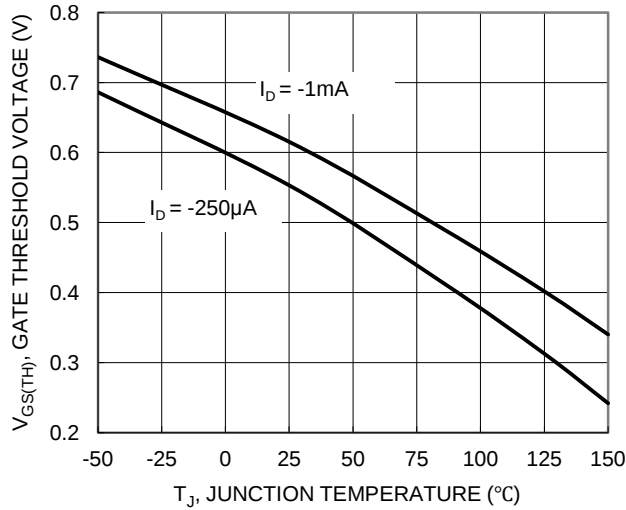


Figure 7. Gate Threshold Variation vs. Junction Temperature

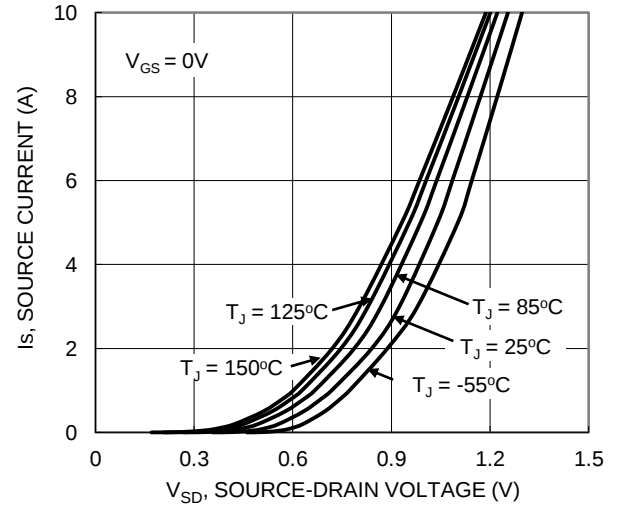


Figure 8. Diode Forward Voltage vs. Current

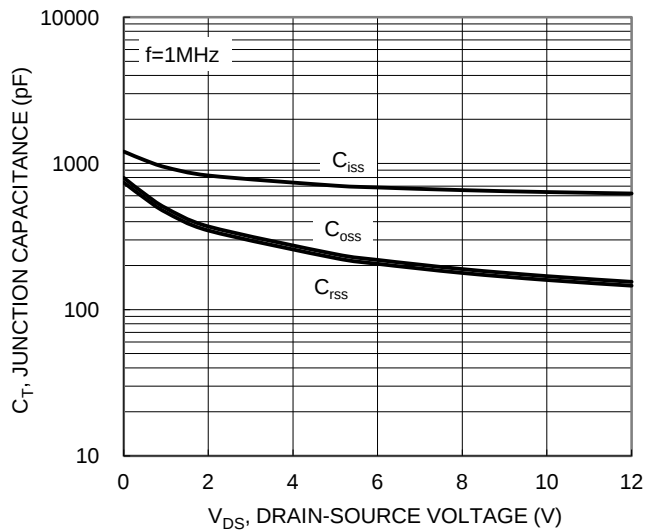


Figure 9. Typical Junction Capacitance

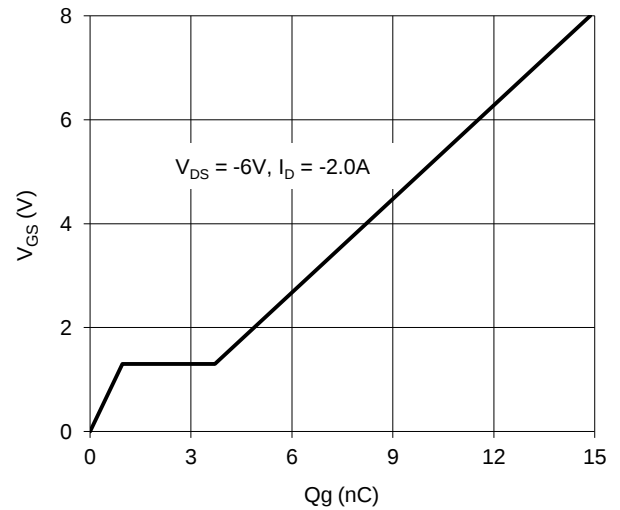


Figure 10. Gate Charge

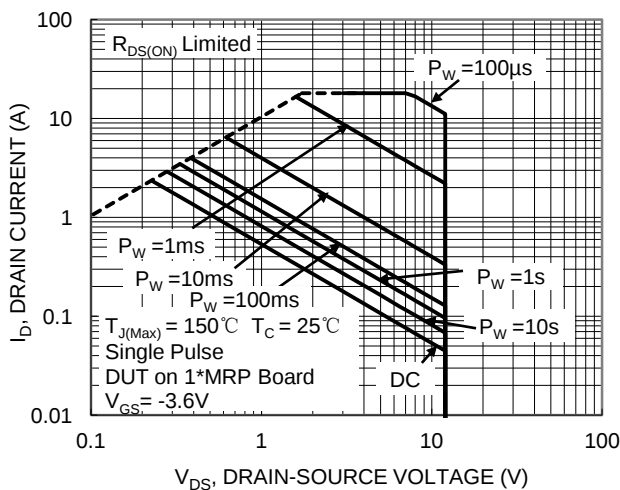


Figure 11. SOA, Safe Operation Area

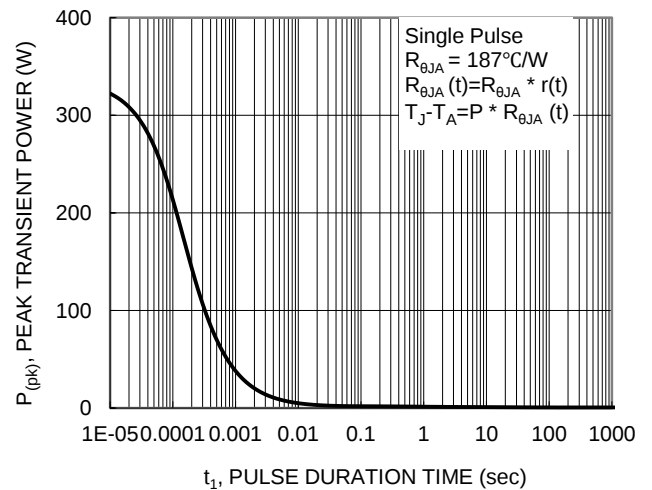


Figure 12. Single Pulse Maximum Power Dissipation

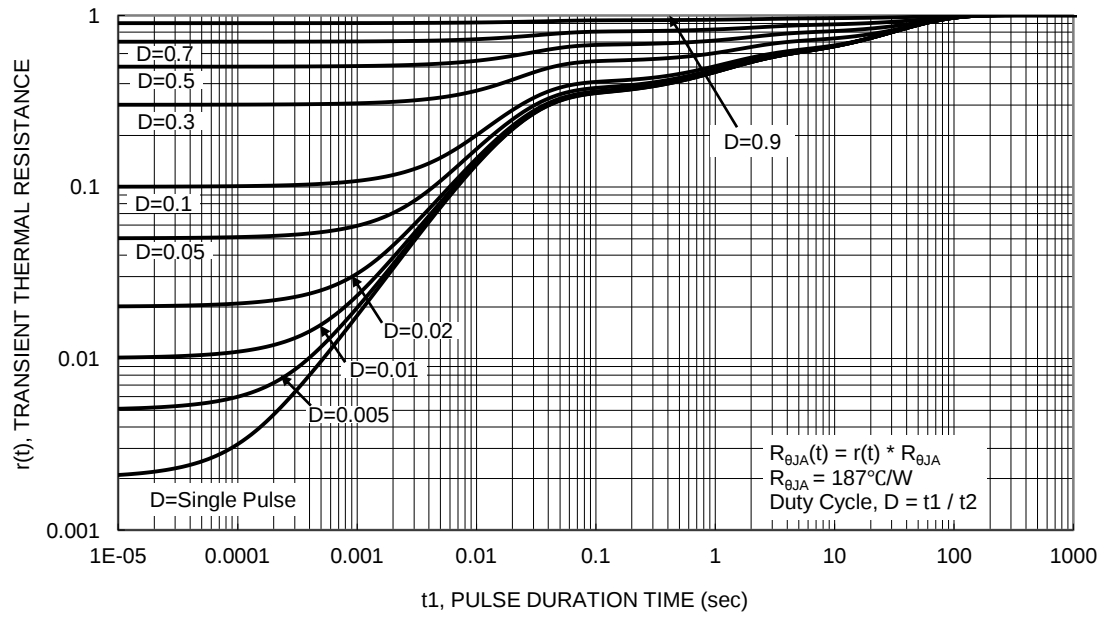
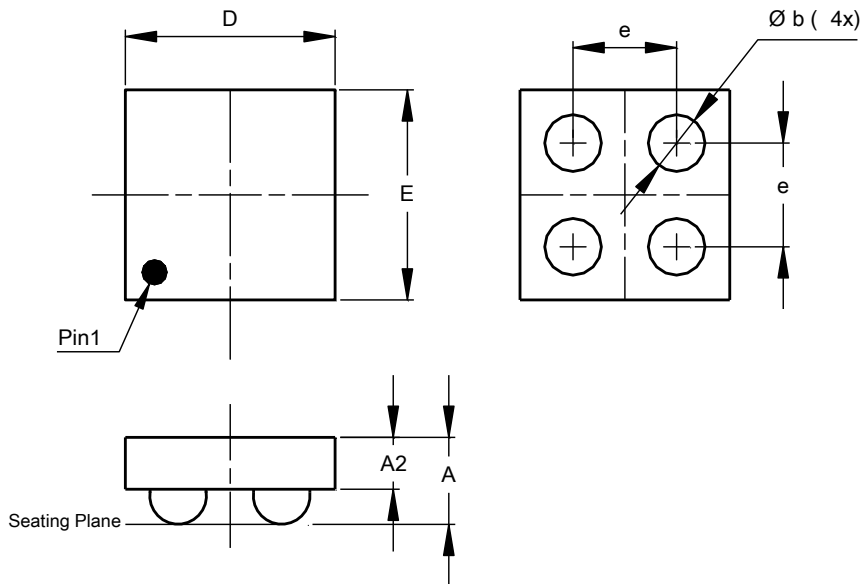


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-WLB0808-4

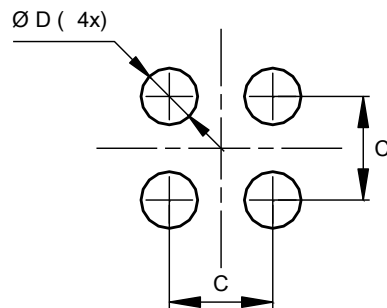


X2-WLB0808-4			
Dim	Min	Max	Typ
A	--	0.400	0.375
A2	--	--	0.180
b	0.1971	0.2409	0.219
D	0.790	0.820	0.816
E	0.790	0.820	0.816
e	--	--	0.400
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-WLB0808-4



Dimensions	Value (in mm)
C	0.400
D	0.219

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